

## DESCRIPTION

The HT9435 uses advanced technology to provide excellent  $R_{DS(on)}$ , low switching loss and reasonable price.

This high density process is especially tailored to minimize on-state resistance. These devices are particularly suited for low voltage application such as cellular phone and notebook computer power management and other battery powered circuits, and low in-line power loss are needed in a very small outline surface mount package.

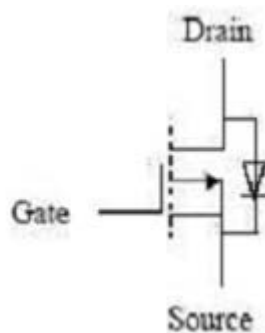
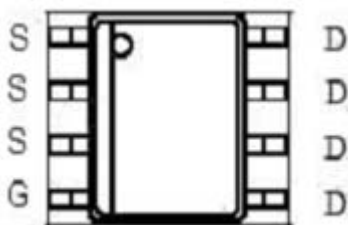
## FEATURES

- ◆ -30V/-5.1A,  $R_{DS(ON)} = 50m\Omega @ V_{GS} = -10V$
- ◆ -30V/-3.6A,  $R_{DS(ON)} = 95m\Omega @ V_{GS} = -4.5V$
- ◆ Super high dense cell design for low  $R_{DS(ON)}$
- ◆ Rugged and reliable
- ◆ SOP-8 package design

## APPLICATIONS

- ◆ POWER Management in Note
- ◆ Portable Equipment
- ◆ Battery Powered System
- ◆ DC/DC Converter
- ◆ LCD Display

## PIN CONFIGURATION



## ABSOLUTE MAXIMUM RATINGS

( $T_A=25\text{ }^\circ\text{C}$  Unless Otherwise Noted)

| Parameter                             |                | Symbol    | Maximum    | Unit             |
|---------------------------------------|----------------|-----------|------------|------------------|
| Drain-Source Voltage                  |                | $V_{DS}$  | -30        | V                |
| Gate-Source Voltage                   |                | $V_{GS}$  | $\pm 25$   | V                |
| Drain Current                         | Continuous (1) | $I_D$     | -5.1       | A                |
|                                       | Pulse (2)      | $I_{DM}$  | -20        |                  |
| Drain-Source Diode Forward Current(1) |                | $I_s$     | -2.6       | A                |
| Maximum Power Dissipation (1)         |                | $P_D$     | 2.5        | W                |
| Operating junction temperature range  |                | $T_J$     | 150        | $^\circ\text{C}$ |
| Storage temperature range             |                | $T_{STG}$ | -55 to 150 | $^\circ\text{C}$ |

## THERMAL RESISTANCE RATINGS

| Thermal Resistance  | Symbol         | Maximum | Unit                        |
|---------------------|----------------|---------|-----------------------------|
| Junction-to-Ambient | $R\theta_{JA}$ | 50      | $^{\circ}\text{C}/\text{W}$ |

**Note :**

1. Surface Mounted on FR4 Board ,  $t \leq 10\text{sec}$
2. Pulse Test: Pulse width  $\leq 300\mu\text{s}$  , Duty Cycle  $\leq 2\%$

## ELECTRICAL CHARACTERISTICS

( $T_A=25^{\circ}\text{C}$  Unless Otherwise Noted)

| Parameter                                     | Symbol       | Test Conditions   | Min  | Typ   | Max       | Units         |
|---|--------------|---|------|-------|-----------|---------------|
| <b>Off Characteristics</b>                    |              |   |      |       |           |               |
| Drain-Source Breakdown Voltage                | $BV_{DSS}$   | $V_{GS} = 0\text{V}, I_D = -250\mu\text{A}$   | -30  | -     | -         | V             |
| Zero Gate Voltage Drain Current               | $I_{DSS}$    | $V_{DS} = -24\text{V}, V_{GS} = 0\text{V}$  | -    | -     | -1        | $\mu\text{A}$ |
| Gate-Body Leakage                             | $I_{GSS}$    | $V_{DS} = 0\text{V}, V_{GS} = \pm 25\text{V}$   | -    | -     | $\pm 100$ | nA            |
| <b>On Characteristics (1)</b>                 |              |   |      |       |           |               |
| Gate Threshold Voltage                        | $V_{GS(th)}$ | $V_{GS} = V_{DS}, I_D = -250\mu\text{A}$  | -1.2 | -1.8  | -2.4      | V             |
| Drain-Source On State Resistance              | $R_{DS(ON)}$ | $V_{GS} = -10\text{V}, I_D = -5.1\text{A}$  | -    | 40    | 50        | m $\Omega$    |
|   |              | $V_{GS} = -4.5\text{V}, I_D = -3.6\text{A}$   | -    | 67    | 95        |               |
| <b>Drain-Source Diode Characteristics (1)</b> |              |   |      |       |           |               |
| Diode Forward Voltage                         | $V_{SD}$     | $I_S = -1.0\text{A}, V_{GS} = 0\text{V}$  | -    | -     | -1.0      | V             |
| <b>Dynamic Parameters (2)</b>                 |              |   |      |       |           |               |
| Input Cap.                                    | $C_{iss}$    | $V_{DS} = -15\text{V}, V_{GS} = 0\text{V}$<br>$f = 1\text{MHz}$                                 | -    | 910   | -         | pF            |
| Output Cap.                                   | $C_{oss}$    |   | -    | 170   | -         |               |
| Reverse Transfer Cap                          | $C_{rss}$    |   | -    | 120   | -         |               |
| <b>Switching Parameters (2)</b>               |              |   |      |       |           |               |
| Total Gate Charge                             | $Q_g$        | $V_{DS} = -15\text{V}, V_{GS} = -10\text{V}, I_D = -1\text{A}$                                  | -    | 17.4  | -         | nC            |
|   |              | $V_{DS} = -15\text{V}, V_{GS} = -4.5\text{V}, I_D = -1\text{A}$                                 | -    | 9.1   | -         |               |
| Gate-Source Charge                            | $Q_{gs}$     | $V_{DS} = -15\text{V}, V_{GS} = -10\text{V}, I_D = -1\text{A}$                                  | -    | 3.1   | -         | nS            |
| Gate-Drain Charge                             | $Q_{gd}$     |   | -    | 3.5   | -         |               |
| Turn-On Time                                  | $T_{D(on)}$  | $V_{DS} = -15\text{V}, R_L = 15\Omega, I_D = -1\text{A}, V_{GEN} = -10\text{V}, R_G = 10\Omega$ | -    | 5.36  | -         |               |
|   | $T_r$        |   | -    | 7.76  | -         |               |
| Turn-Off Time                                 | $T_{D(off)}$ |   | -    | 15.84 | -         |               |
|   | $T_f$        |   | -    | 9.84  | -         |               |

**Note :**

1. Pulse Test: Pulse width  $\leq 300\mu\text{s}$  , Duty Cycle  $\leq 2\%$
2. Guaranteed by design, not subject to production testing

## TYPICAL CHARACTERISTICS

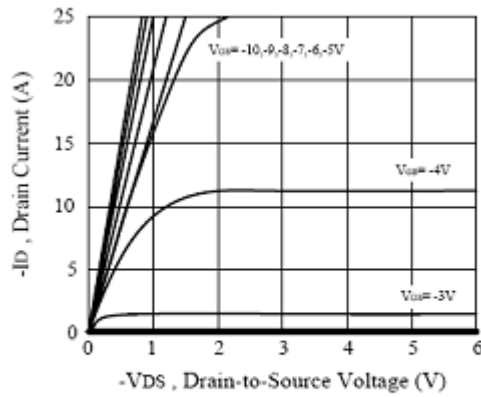


Figure 1. Output Characteristics

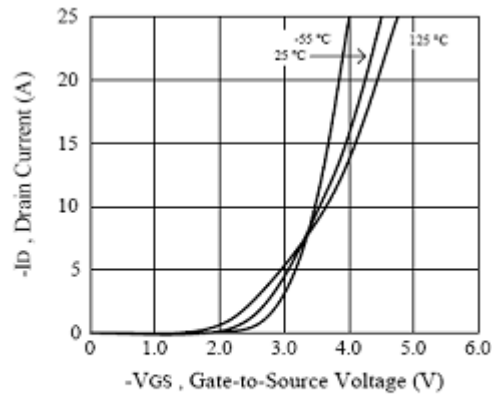


Figure 2. Transfer Characteristics

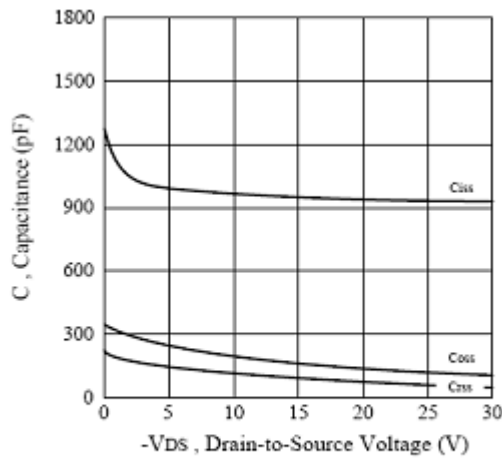


Figure 3. Capacitance

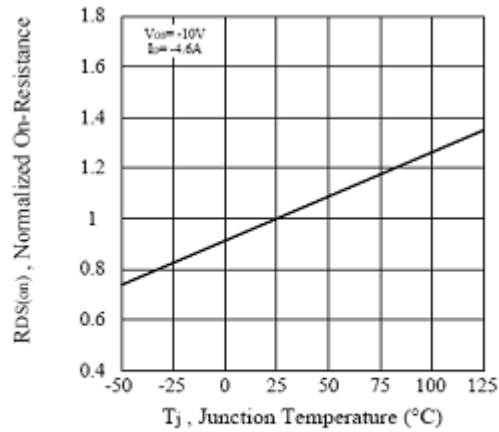


Figure 4. On-Resistance Variation with Temperature

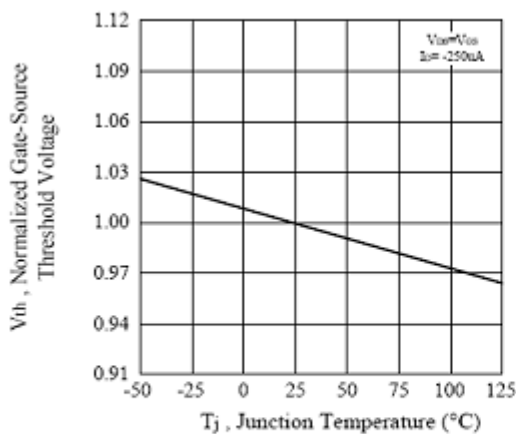


Figure 5. Gate Threshold Variation with Temperature

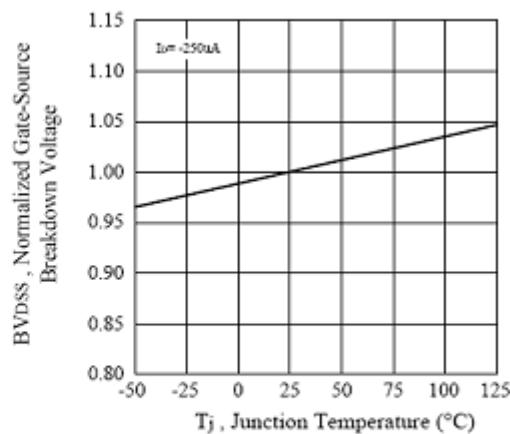
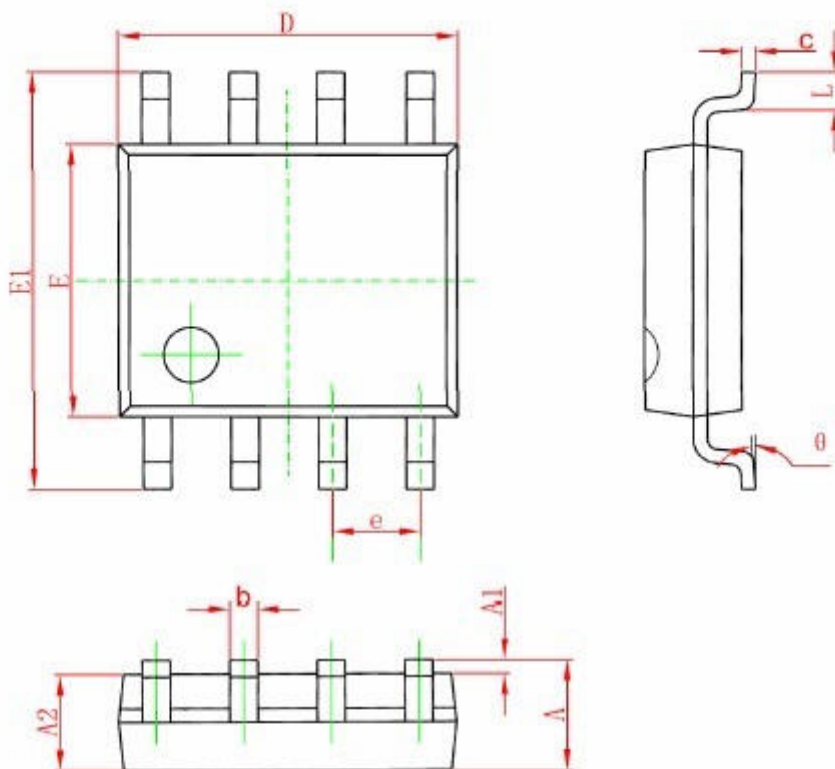


Figure 6. Breakdown Voltage Variation with Temperature



## PACKAGE DESCRIPTION

### SOP8 PACKAGE OUTLINE DIMENSIONS



| Symbol | Dimensions In Millimeters |       | Dimensions In Inches |       |
|--------|---------------------------|-------|----------------------|-------|
|        | Min                       | Max   | Min                  | Max   |
| A      | 1.350                     | 1.750 | 0.053                | 0.069 |
| A1     | 0.100                     | 0.250 | 0.004                | 0.010 |
| A2     | 1.350                     | 1.550 | 0.053                | 0.061 |
| b      | 0.330                     | 0.510 | 0.013                | 0.020 |
| c      | 0.170                     | 0.250 | 0.006                | 0.010 |
| D      | 4.700                     | 5.100 | 0.185                | 0.200 |
| E      | 3.800                     | 4.000 | 0.150                | 0.157 |
| E1     | 5.800                     | 6.200 | 0.228                | 0.244 |
| e      | 1.270 (BSC)               |       | 0.050 (BSC)          |       |
| L      | 0.400                     | 1.270 | 0.016                | 0.050 |
| θ      | 0°                        | 8°    | 0°                   | 8°    |